Ordering number: EN 2848

SANYO No.2848

2SC4425

NPN Triple Diffused Planar Silicon Transistor

Switching Regulator Applications

Features

- High breakdown voltage, high reliability
- Fast switching speed (t_f: 0.1μs typ)
- Wide ASO
- Adoption of MBIT process
- Micaless package facilitating easy mounting

Absolute Maximum Ratings at Ta = 25°C

				unit
Collector-to-Base Voltage	V_{CBO}		500	V
Collector-to-Emitter Voltage	V_{CEO}		400	V
Emitter-to-Base Voltage	V_{EBO}		7	V
Collector Current	I_C		25	A
Peak Collector Current	i_{cp}	PW≦300μs, duty cycle ≦10%	40	A
Base Current	I_B		8	A
Collector Dissipation	P_C		3	W
		T_C = 25°C	65	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta = 25°C

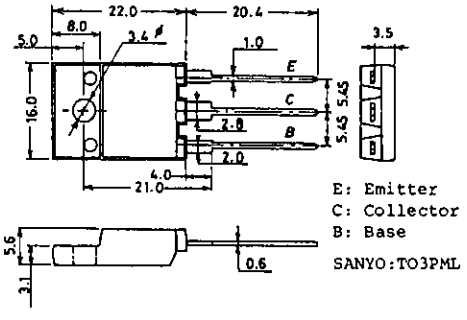
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 400V, I_E = 0			10	μA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 5V, I_C = 0			10	μA
DC Current Gain	$h_{FE}(1)$*	V_{CE} = 5V, I_C = 3.2A	15		50	
	$h_{FE}(2)$	V_{CE} = 5V, I_C = 16A	10			
	$h_{FE}(3)$	V_{CE} = 5V, I_C = 10mA	10			
C-E Saturation Voltage	$V_{CE(sat)}$	I_C = 16A, I_B = 3.2A			0.8	V
B-E Saturation Voltage	$V_{BE(sat)}$	I_C = 16A, I_B = 3.2A			1.5	V
Gain-Bandwidth Product	f_T	V_{CE} = 10V, I_C = 3.2A		20		MHz
Output Capacitance	c_{ob}	V_{CB} = 10V, f = 1MHz		300		pF
C-B Breakdown Voltage	$V_{(BR)CBO}$	I_C = 1mA, I_E = 0	500			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	I_C = 10mA, R_{BE} = ∞	400			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	I_E = 1mA, I_C = 0	7			V
C-E Sustain Voltage	$V_{CEX(sus)}$	I_C = 10A, I_{B1} = 1A I_{B2} = −4A, L = 200μH, clamped	400			V

Continued on next page.

* : The $h_{FE}(1)$ of the 2SC4425 is classified as follows. When specifying the $h_{FE}(1)$ rank, specify two ranks or more in principle.

15 L 30	20 M 40	30 N 50

Package Dimensions 2039
(unit : mm)



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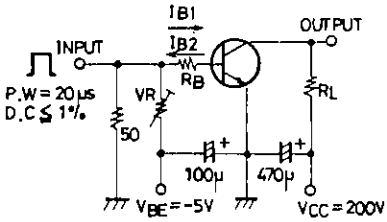
			min	typ	max	unit
Turn-on Time	t_{on}	$I_C=20A, I_{B1}=4A$ $I_{B2}=-8A, R_L=10\Omega$ $V_{CC}=200V$			0.5	μs
Storage Time	t_{stg}				2.5	μs
Fall Time	t_f				0.3	μs

Switching Time Test Circuit



Unit (Resistance : Ω, Capacitance : F)